Non-metal to Metal Transitions

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Fujimori, Electronic structure of metallic oxides: band-gap closure and valence control, *J. Phys. Chem. Solids* **53** (1992) 1595–1602.

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Purpose of this course – understanding the diagram below:



Fujimori, Electronic structure of metallic oxides: band-gap closure and valence control, *J. Phys. Chem. Solids* **53** (1992) 1595–1602.

See also: Imada, Fujimori, and Tokura, Metal-insulator transitions, *Rev. Mod. Phys.* **70** (1998) 1039–1263.

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An example of non-metal to metal transitions: The Periodic Table



Why are most elements metallic, but not all?



6-order of magnitude resistivity change over a 10 K range in the vicinity of 340 K, in $V_{0.976}Cr_{0.024}O_2$

Marezio, McWhan, Remeika, Dernier, Structural aspects of the metal-insulator transitions in Cr-doped VO₂, *Phys. Rev. B* **5** (1972) 2541–2551.

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Valence-precise compounds. Counting electrons in TiO₂: Assign as Ti⁴⁺ and O²⁻



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Insulator, not so easy to dope.

Counting electrons in SnO₂: Assign as Sn⁴⁺ and O²⁻ (more covalent than TiO₂)



Semiconductor: Easier to dope. Used as a TCO material.

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Counting electrons in BaPbO₃: Assign as Pb⁴⁺ and O²⁻. An unexpected semi-metal



A surprise – it's a (semi)metal. The equivalent Sn⁴⁺ compound is not.

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MoS₂: Crystal-field effects are important (and therefore structure).



It's a semiconductor because the two d electrons occupy a (filled) d_z^2 orbital.

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 MoS_2 in the TaS₂ structure: Octahedral coordination means a metal.



The two d electrons are now in a degenerate band.

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Another example of crystal-field effects: PdO



Square-planar d⁸ configuration allows a band insulator.

Kurzman, Miao, Seshadri, Hybrid functional electronic structure of PbPdO₂, a small- gap semiconductor, J. Phys.: Condens. Matter 23 (2011) 465501(1–7).

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The Wilson (Arthur Herries Wilson) theory:

Partially filled bands allow electrons to move, and this increases the zero-point energy (the Heisenberg uncertainty principle).

If the band were filled, the Pauli exclusion principle would ensure that any movement (of electrons) is precisely compensated.

However: "... overlap of the wave functions gives rise to a half-filled band, and according to the Wilson picture, the system should be metallic-however far apart the atoms might be."

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Wilson, The Theory of Metals. I, *Proc. R. Soc. London. Ser. A* **138** (1932) 594–606. Quote from: Edwards and Sienko, The transition to the metallic state, *Acc. Chem. Res.* **15** (1982) 87–93.

Thomas-Fermi screening:

Consider the density of electrons in a metal: These are of the order of 10²² cm⁻³, which is as dense as a condensed (crystalline phase). If we expected these electrons to strongly repel, they should crystallize (like hard spheres do).

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How is it that they go about their business like other electrons were not there.

Answer: They do NOT interact through the Coulomb (1/r) potential !

The Screened Coulomb Potential (after Kittel):

$$\varphi = \frac{q}{r} \exp(-k_s r)$$

 $k_{\rm s}$ is the Thomas-Fermi screening wavelength:

$$k_s = 4\pi e^2 D(\epsilon_F)$$

Thomas-Fermi screening: The counterintuitive role of the density of states

$$\varphi = \frac{q}{r} \exp(-k_s r)$$
 with $k_s = 4\pi e^2 D(\epsilon_F)$

The larger the densities of state, the more electrons are screened. See image below from Kittel (8th Edn. page 407).



Also:

 k_s a_0

where a_0 is the Bohr radius and n_0 is the concentration of charge carriers.

For Cu metal, $n_0 = 8.5 \times 10^{22} \text{ cm}^{-3}$ and $1/k_{\rm s} = 0.55$ Å. It is only below this distance that electrons "talk".

So more electrons in a limited volume means the less they "see" each other.

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The Herzfeld criterion and the periodic table

The Clausius-Mossotti equation relates the relative dielectric ε_r constant of matter to the molar refractivity R_m in the gaseous state, and the molar volume V_m in condensed phase.

$$\frac{\epsilon_r - 1}{\epsilon_r + 2} = \frac{R}{V} \text{ which means that } \frac{R}{V} = 1 \implies \epsilon_r = \infty$$

This is the condition of a metal (infinite dielectric screening).

Since *R* and *V* are properties of the atom, this allows the periodic table to be sorted (see next page).

Edwards and Sienko, The transition to the metallic state, Acc. Chem. Res. 15 (1982) 87–93.

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The Herzfeld criterion and the periodic table



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The Peierls distortion seen in 1D chains: The simplest model for a gap.



Note that we go from being valence-imprecise to being valence precise: Now two electrons per unit cell.

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A real-world example of Peierls:



Knappschneider *et al.*, Peierls-distorted monoclinic MnB₄ with a Mn-Mn bond, *Angew. Chem. Int. Ed.* **53** (2014) 1684–1688.

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Charge carrier concentration and the filling-driven Mott transition



Band theory (Wilson theory) and DFT would suggest that any departure from a band insulator should give rise to metallic behavior. This is wrong. Look close to SrTiO₃ and CaTiO₃.

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Consider the 1D chain again, at half-filling. Assume Peierls does not take place.

The system remains metallic no matter how far apart the atoms, which cannot be right. Mott: "... this is against common experience, and, one might say, common sense"



Charge carrier concentration and the filling-driven Mott transition

This familiar picture of atomic orbital levels interacting and spreading out as they approach, is not a band-structure picture. This picture captures the Herzfeld criterion discussed previously.



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Examples of composition (band-filling) dependent non-metal to metal transitions:



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Consider the case of expanded Cs, which for convenience, can be treated as a chain. When the atoms are infinitely separated, the energy required to remove an electron is the ionization energy IE = 3.89.

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- The energy required to place an electron on neutron Cs is the electron affinity EA = 0.47 eV.
- The energy cost to transfer an electron is the difference, referred to as the Hubbard U.

U = IE - EA = 3.42 eV

- This is the potential energy barrier required to be overcome, in order for electrons to hop.
- Hopping is favored by the kinetic energy or bandwidth.

Charge carrier concentration and the filling-driven Mott transition



Approximate energetics for the metallization of Cs.

Edwards and Sienko, Acc. Chem. Res.

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Charge carrier concentration and the filling-driven Mott transition



Consequences for magnetism: When the charge carriers are localized, they can carry spin.

Magnetism is therefore frequently associated with nonmetal to metal transitions.

Edwards and Sienko, Acc. Chem. Res.

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The Mott treatment of when the threshold concentration is crossed, is based on Thomas-Fermi screening:

$$arphi = rac{q}{r} \exp(-k_s r)$$
 with $k_s \propto rac{n_0^{1/3}}{a_0}$

When the strength of the screening overcomes the Coulombic repulsion U, at a critical number density of carriers n_c and the Mott criterion is fulfilled:

$$n_c^{1/3}a_0 \approx 0.25$$

where a_0 is the hydrogenic Bohr radius.

This should be a first-order phase transition, although that has not been easy to verify.

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Some more examples:



Edwards and Sienko, Acc. Chem. Res.

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Charge carrier concentration and the filling-driven Mott transition



Manifestations of the Mott criterion.

Note that a large Bohr radius should correspond to a high mobility.

Remember:

 $\sigma = ne\mu$

Edwards and Sienko, Acc. Chem. Res.

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But large intrinsic μ is associated with small electronegativity differences.

Adapted from R. E. Newnham, Properties of Materials

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The Mott minimum metallic conductivity (originally argued for disordered systems):

$$n_c^{1/3}a_0 \approx 0.25$$

implies that at the transition:

 $\sigma_{\rm M} = C e^2 / (\hbar a_0)$

This is a fixed value of the conductivity, usually close to 100 S cm⁻¹, or correspondingly, there is a maximum metallic resistivity, close to 0.01 Ω cm.

Möbius, The metal-semiconductor transition in three-dimensional disordered systems-reanalysis of recent experiments for and against minimum metallic conductivity, *J. Phys. C: Solid State Phys.* **18** (1985) 4639–4670.

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Charge carrier concentration and the filling-driven Mott transition



From Imada, Fujimori, and Tokura, Metal-insulator transitions, *Rev. Mod. Phys.* **70** (1998) 1039–1263.



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